ABSTRACT OF THE DISCLOSURE

A nonvolatile semiconductor memory device includes a first memory cell array including electrically re-programmable main memory cells, a second memory cell array including electrically data-programmable redundancy memory cells, a first storage configured to store a specified code, a first comparator configured to compare a selected code with the specified code to generate an activating signal, a faulty address latch circuit configured to be activated by the activating signal and controlled to temporarily latch a fault address corresponding to the fault, a second storage configured to store the faulty address latched by the faulty address latch circuit, a second comparator configured to compare an input address with the faulty address to generate a replacement control signal when the input address coincides with the faulty address, and a replacing circuit configured to replace an output of the first memory cell array with an output of the second memory cell array.